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### **IT-4-P-1565 Imaging of nanoparticles in cells with backscattered electrons in a scanning electron microscope**

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Scanning electron microscopy (SEM) is an established technique for ultrastructure imaging of cells. Backscattered electrons (BSEs) yield subsurface information and atomic-number contrast [1] and are used in this work to image cellular structures and NPs incubated in cells. Specifically, optimum primary electron energies  $E_0$  for BSE imaging were determined for thin cell sections with thicknesses  $100 \text{ nm} \leq t \leq 1000 \text{ nm}$  deposited on indium-tin-oxide (ITO)-covered glass slides which are interesting substrates for correlative light and electron microscopy imaging [2]. We also developed a technique to determine the information depth (ID) which denotes the maximum subsurface depth at which an object can be imaged.

Thin cell sections of HT29 colon carcinoma cells incubated with  $\text{SiO}_2$  nanoparticles (NPs) of 40 nm size were studied (see [3] for sample preparation). Poststaining was omitted to avoid artifacts. SEM was performed with an FEI Quanta 650 FEG with a low-voltage high-contrast detector (vCD).

Small  $E_0$  were selected to limit the escape depth of BSEs because electrons from large sample depths degrade image resolution and contrast. Fig. 1a shows a 2.5 keV BSE image of a 200 nm section. The  $\text{SiO}_2$  NPs, typically contained in vesicles, can be easily detected due to their bright contrast. Cell organelles display high contrast despite the lack of poststaining in Fig. 1b.

Fig. 2a shows a 1  $\mu\text{m}$  section where  $E_0$  up to 7.5 keV can be applied without sample charging. In addition to the incubated  $\text{SiO}_2$  NPs, Au NPs with a size of 40 nm are present on the surface and can be distinguished due to their higher BSE intensity. BSE images were taken at different  $E_0$  between 1.5 and 7.5 keV for depth-dependent detection of  $\text{SiO}_2$  NPs. With increasing  $E_0$  more NPs become visible corresponding to the increasing ID. The depth of NPs from the surface was determined by tilting the sample and applying a triangulation method. In Fig. 2b the experimentally determined particle depths (dots) are plotted as a function of  $E_0$  and are compared with calculated ID values obtained by Monte-Carlo simulations (triangles). Based on the escape depth  $T = f \cdot A \cdot E_0^{1.67} / (\rho \cdot Z^{0.89})$  ( $Z$ : average atomic number,  $A$ : average atomic weight,  $\rho$ : density) proposed in [4], an analytical expression for the ID was obtained by fitting the experimental data with a modified factor  $f$ . This expression allows the determination of the ID of BSEs in biological samples. Experiments with entire cells grown on ITO-coated glass are promising with respect to NP detection and are subject of further work.

#### References

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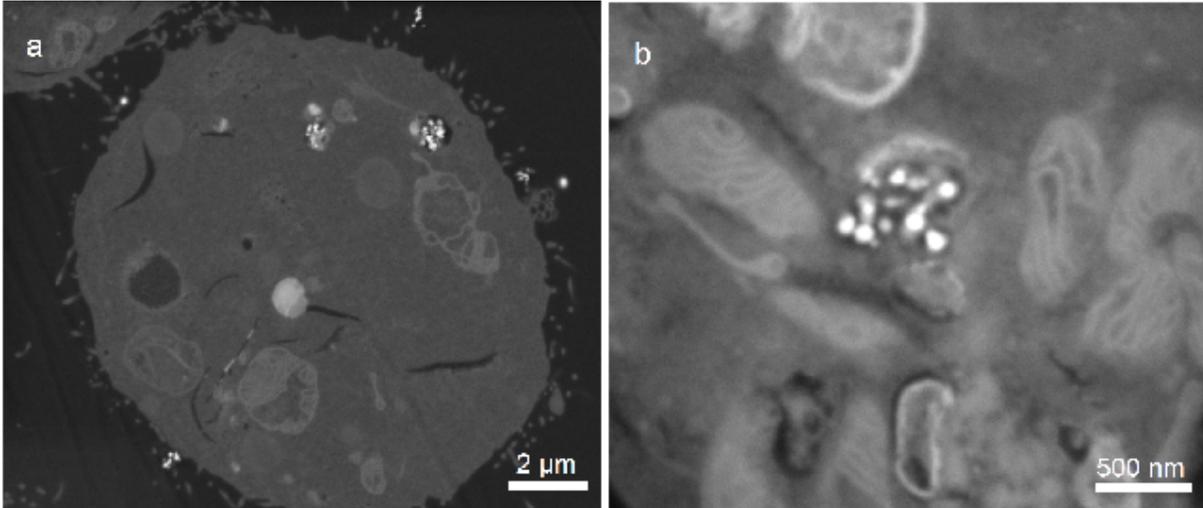


Fig. 1: BSE SEM images of a 200 nm section of an HT29 cell deposited on an ITO-covered glass substrate. (a) Overview image taken at  $E_0 = 2.5$  keV.  $\text{SiO}_2$  NPs and organelles are visible in the cell. (b) High-magnification image taken at  $E_0 = 3.5$  keV. NPs and membranes can be well resolved.

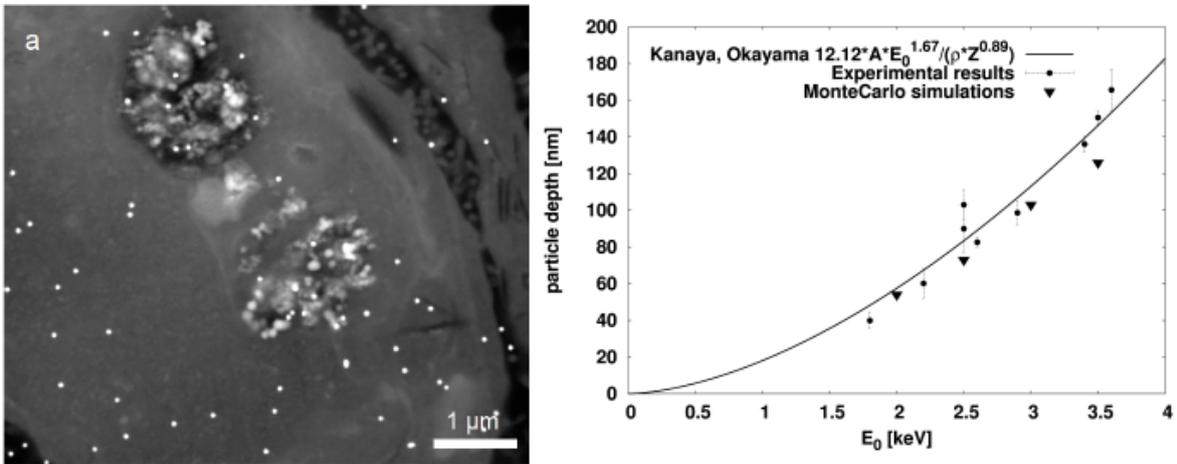


Fig. 2: (a) 7 keV BSE SEM image of a 1000 nm section of an HT29 cell.  $\text{SiO}_2$  and Au NPs show different contrast compared to the cell matrix. (b) Plot of the information depth as a function of  $E_0$  with experimentally determined values (dots) and Monte Carlo simulations (triangles). Fit curves are based on the modified Kanaya-Okayama equation [4].